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SEMICONDUCTOR®

FQB33N10L N-Channel QFET[®] MOSFET

100 V, 33 A, 52 m Ω

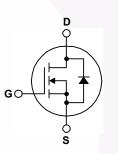
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 33 A, 100 V, $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ = 52 m Ω (Max) @V_{\mathsf{GS}} = 10 V, I_D = 16.5 A
- Low Gate Charge (Typ. 30 nC)
- Low Crss (Typ. 70 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted

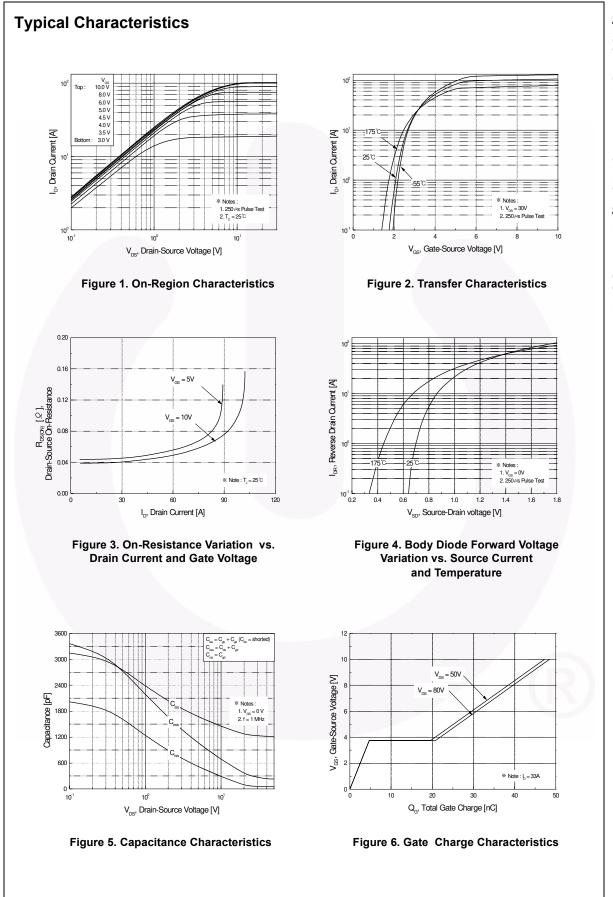
Symbol	Parameter		FQB33N10LTM	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		33	A
	- Continuous (T _C = 10	23	A	
I _{DM}	Drain Current - Pulsed (Note 1)		132	Α
V _{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		430	mJ
I _{AR}	Avalanche Current	(Note 1)	33	A
E _{AR}	Repetitive Avalanche Energy (Note 1		12.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.75	W
	Power Dissipation $(T_C = 25^{\circ}C)$		127	W
	- Derate above 25°C		0.85	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
ΤL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

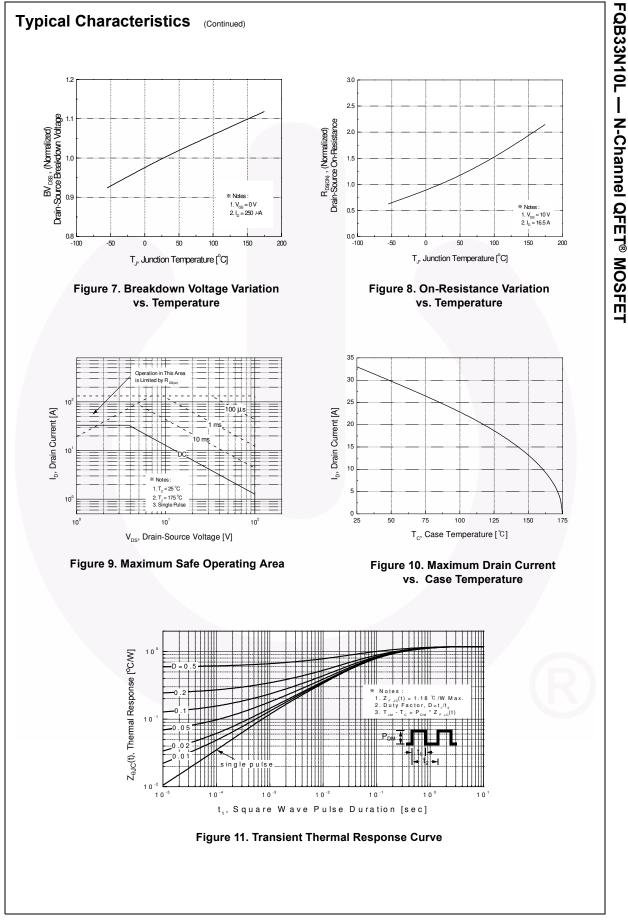
Thermal Characteristics

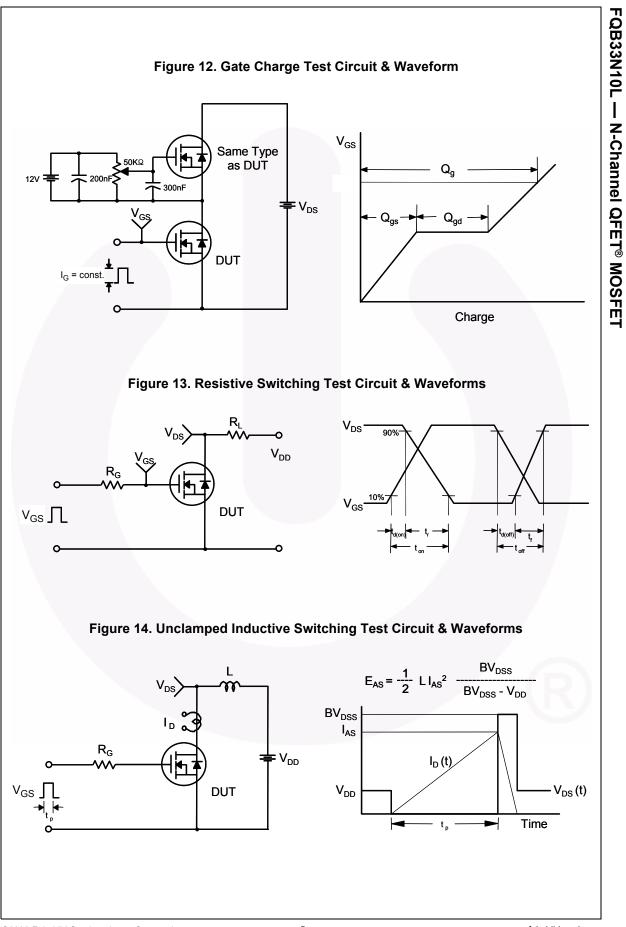
Symbol	Parameter	FQB33N10LTM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max	1.18	
D	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (* 1 in ² pad of 2 oz copper), Max.	40	

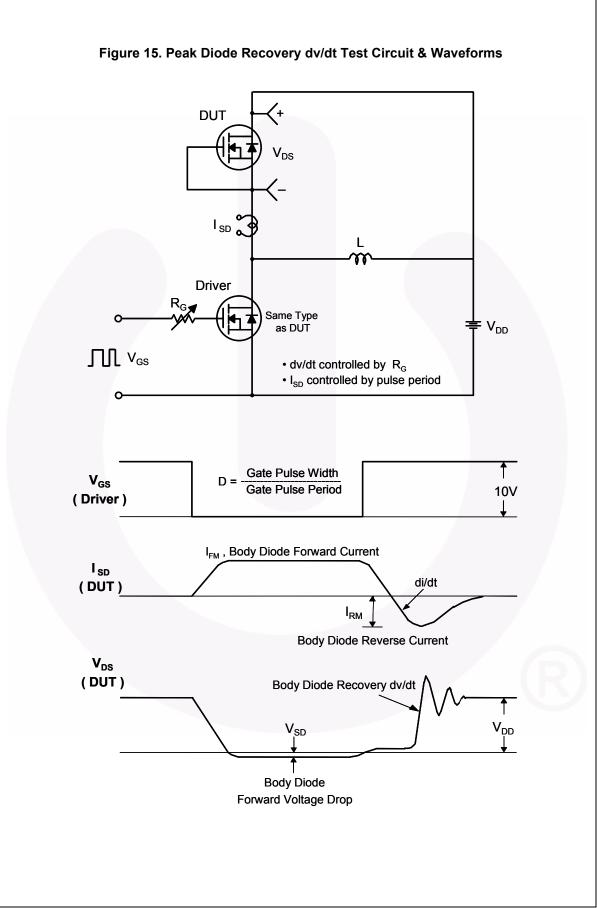
October 2013

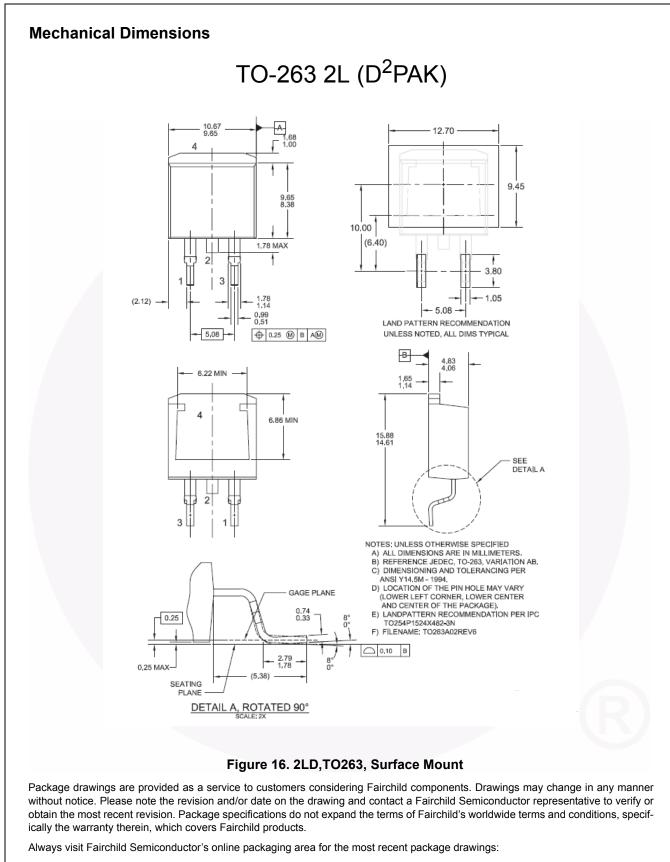
EOP3	Device Marking Device		PackageReel SizeD2-PAK330mm		Tape Width24mm		dth	Quantity
FQB33N10L FQB33N10L		FQB33N10LTM						800
lectric	cal Char	racteristics T _c = 25°C	unless otherwise noted					
Symbol		Parameter	Test Con	ditions	Min	Тур	Мах	Unit
	aracteristi	66				•		
BV _{DSS}		ce Breakdown Voltage	$V_{GS} = 0 V, I_D = 25$	50 μA	100			V
ABV _{DSS}	Breakdown Voltage Temperature		I _D = 250 μA, Refe			0.09		V/°C
$/ \Delta T_J$	Coefficient							
	Zero Gate	Voltage Drain Current	$V_{DS} = 100 V, V_{GS}$				1	μΑ
	Oata Daalu	Leeleese Ouwent Ferried	$V_{DS} = 80 \text{ V}, \text{ T}_{C} = 100 \text{ V}$				10	μA
GSSF	Gate-Body Leakage Current, Forward		$V_{GS} = 20 V, V_{DS} = 0 V$ $V_{GS} = -20 V, V_{DS} = 0 V$				100	nA
GSSR	Gate-Body	Leakage Current, Reverse	$v_{GS} = -20 v, v_{DS}$	= 0 V			-100	nA
	racteristi	cs			1	I		_
V _{GS(th)}	Gate Three	shold Voltage	$V_{DS} = V_{GS}, I_D = 2$		1.0		2.0	V
R _{DS(on)}	Static Drain		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1$			0.039	0.052	Ω
	On-Resista		$V_{GS} = 5 V, I_D = 16$			0.043	0.055	
9FS	Forward Tr	ansconductance	$V_{DS} = 30 V, I_{D} = 1$	6.5 A		27		S
Dynami	ic Charac	teristics						
C _{iss}	Input Capa		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			1250	1630	pF
C _{oss}	Output Ca	pacitance				305	400	pF
								P
C _{rss}	Reverse Tr	ransfer Capacitance	-			70	90	pF
						70	90	
Switchi		cteristics		20.4		70	90 45	
	ing Chara	cteristics elay Time	$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 3$	33 A,				pF
Switchi d(on) r	i ng Chara Turn-On D	cteristics elay Time ise Time	- V _{DD} = 50 V, I _D = 3 - R _G = 25 Ω	33 A,		17	45	ns
Switchi d(on) r d(off)	i ng Chara Turn-On D Turn-On R	cteristics elay Time ise Time elay Time		33 A, (Note 4)		17 470	45 950	ns ns
Switchi d(on) r d(off) f	i ng Chara Turn-On D Turn-On R Turn-Off D	cteristics elay Time ise Time elay Time all Time	R _G = 25 Ω	(Note 4)		17 470 70	45 950 150	pF ns ns ns
Switchi G(on) G(off) Ggg	ng Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa	cteristics elay Time ise Time elay Time all Time Charge	$R_{G} = 25 \Omega$ V _{DS} = 80 V, I _D = 3	(Note 4)		17 470 70 120	45 950 150 250	pF ns ns ns ns
Switchi t _{d(on)}	ng Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate	cteristics elay Time ise Time elay Time all Time Charge ce Charge	R _G = 25 Ω	(Note 4)	 	17 470 70 120 30	45 950 150 250 40	pF ns ns ns ns nC
Switchi tr tr tr Qg Qgs Qgs Qgd	ng Chara Turn-On D Turn-Off D Turn-Off Fa Total Gate Gate-Soura Gate-Drain	cteristics elay Time ise Time elay Time all Time Charge ce Charge o Charge	$R_{G} = 25 \Omega$ V _{DS} = 80 V, I _D = 3 V _{GS} = 5 V	(Note 4) 33 A, (Note 4)		17 470 70 120 30 4.7	45 950 150 250 40 	ns ns ns ns nC nC
Switchi ^t d(on) tr td(off) tf Qg Qgs Qgs Qgd Drain-S	Ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sourd Gate-Drain	cteristics elay Time ise Time elay Time all Time Charge ce Charge	$R_G = 25 \Omega$ V _{DS} = 80 V, I _D = 3 V _{GS} = 5 V	(Note 4) 03 A, (Note 4) atings		17 470 70 120 30 4.7	45 950 150 250 40 	pF ns ns ns nC nC nC
Switchi ^I d(on) ^I r ^I d(off) ^I f Qg Qgs Qgs Qgd Drain-S	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sourc Gate-Drain Cource Dia	cteristics elay Time ise Time elay Time all Time Charge ce Charge ocharge ocharge	$R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 3$ $V_{GS} = 5 V$ The Maximum Reside Forward Current	(Note 4) 03 A, (Note 4) atings		17 470 70 120 30 4.7 16	45 950 150 250 40 	ns ns ns ns nC nC
Switchi ^t d(on) tr d(off) tf Qg Qgs Qgd Drain-S s SM	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sourc Gate-Drain Gate-Drain Maximum	cteristics elay Time ise Time elay Time all Time Charge ce Charge charge charge charge	$R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 3$ $V_{GS} = 5 V$ hd Maximum R orde Forward Current	(Note 4) B3 A, (Note 4) atings t	 	17 470 70 120 30 4.7 16	45 950 150 250 40 33	PF ns ns ns nC nC nC A
Switchi ^I d(on) ^I r ^I d(off) ^I f Qg Qgs Qgs Qgd Drain-S	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sourc Gate-Drain Source Did Maximum Maximum Drain-Sour	cteristics elay Time ise Time elay Time all Time Charge ce Charge charge charge Dde Characteristics ar Continuous Drain-Source Dic Pulsed Drain-Source Diode F	$R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 3$ $V_{GS} = 5 V$ The Maximum Reside Forward Current	(Note 4) 33 A, (Note 4) atings t	 	17 470 70 120 30 4.7 16	45 950 150 250 40 33 132	pF ns ns ns nc nC nC A











http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002

Dimension in Millimeters



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